







NPN LOW $V_{\text{CE(sat)}}$ TRANSISTOR IN SOT-23

Features

- BV_{CEO} > 25V
- BV_{CBO} > 35V
- I_{C(cont)} = 3A Continuous Currrent
- V_{CE(sat)} < 120mV @ 1A
- R_{CE(sat)} = 77 mΩ
- $P_D = 0.725W$
- 6A Peak Pulse Current
- 25V Forward Blocking Voltage
- Complementary part number ZXTP749F
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Devices (Note 2)

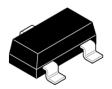
Applications

- MOSFET gate drivers
- Power switches
- Motor control

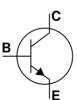
Mechanical Data

- Case: SOT-23
- Case material: molded Plastic. "Green" molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.008 grams (approximate)

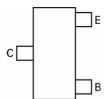
SOT-23



Top View



Device symbol



Pin Configuration

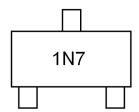
Ordering Information

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN649FTA	1N7	7	8mm	3000

Notes:

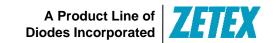
- 1. No purposefully added lead. Halogen and Antimony Free.
- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



1N7 = Product type Marking Code





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Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	35	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current (Note 3)	Ic	3	Α
Peak Pulse Current	I _{CM}	6	Α
Base Current	I _B	500	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = 25°C (Note 4)	P_{D}	725	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C	$R_{ heta JA}$	172	°C/W
Thermal Resistance, Junction to Lead @ T _A = 25°C	$R_{ hetaJL}$	79	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes:

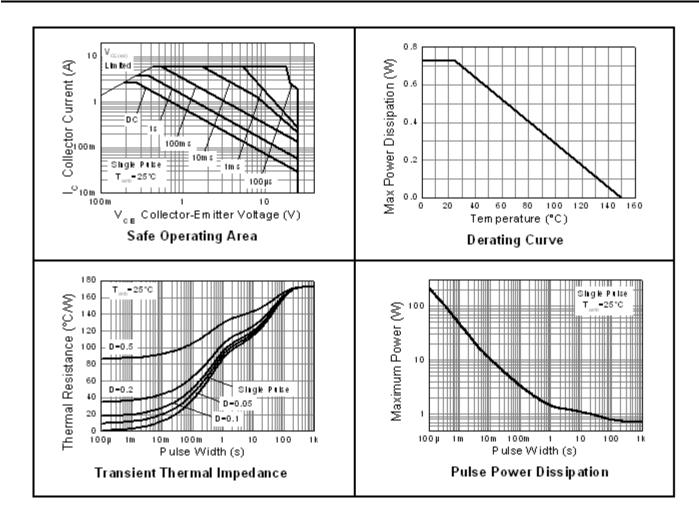
- 3. For a device surface mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions 4. For device mounted on FR4 PCB measured at $t \le 2$ Secs.





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Thermal Characteristics and Derating information







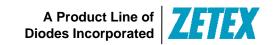
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Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	35	110		V	$I_C = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 5)	$V_{(BR)CEO}$	25	35		V	$I_C = 10 \text{ mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7	8.1		V	$I_E = 100 \mu A$
Collector Cutoff Current	I _{CBO}		< 1	50 0.5	nΑ μΑ	V _{CB} = 28V V _{CB} = 28V, T _{amb} =100 °C
Emitter Cutoff Current	I _{EBO}		< 1	50	. nA	$V_{EB} = 5.6V$
Static Forward Current Transfer Ratio (Note 5)	h _{FE}	200 175 155 50	320 280 250 85	500		I _C = 100mA, V _{CE} = 2V I _C = 1A, V _{CE} = 2V I _C = 2A, V _{CE} = 2V I _C = 6A, V _{CE} = 2V
Collector-Emitter Saturation Voltage (Note 5)	V _{CE(sat)}		70 200	120 300	mV mV	$I_C = 1A$, $I_B = 100 \text{mV}$ $I_C = 3A$, $I_B = 300 \text{mV}$
Base-Emitter Turn-On Voltage (Note 5)	$V_{BE(on)}$		780	850	mV	$I_C = 1A$, $V_{CE} = 2V$
Base-Emitter Saturation Voltage (Note 5)	V _{BE(sat)}		900	1000	mV	$I_C = 1A$, $I_B = 100 \text{mV}$

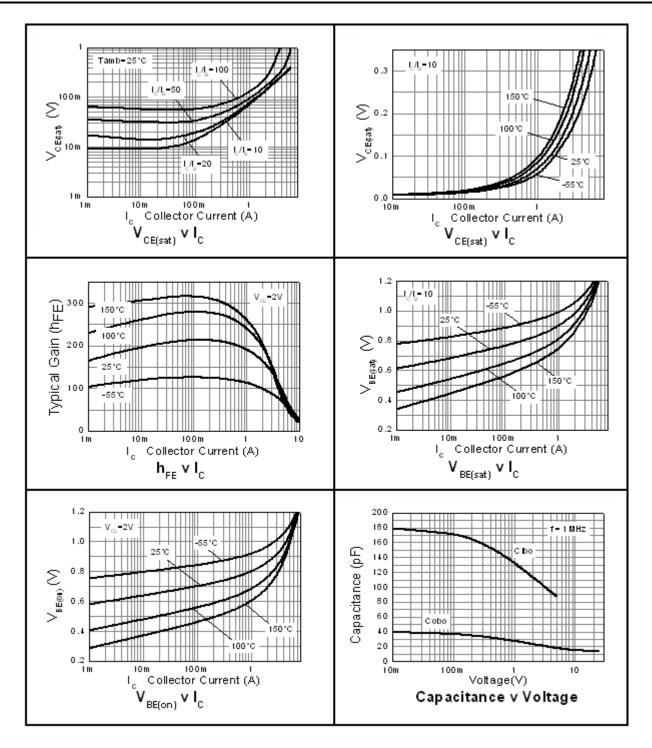
Notes: 5. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%



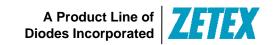


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Typical Characteristics

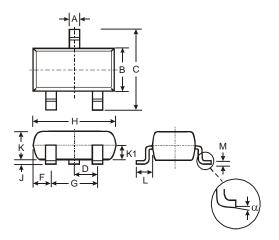






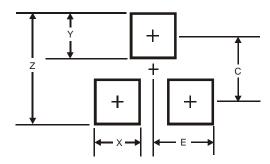
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Package Outline Dimensions



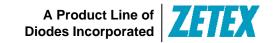
SOT-23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Η	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)		
Z	2.9		
Х	0.8		
Y	0.9		
С	2.0		
E	1.35		





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